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### **Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems**

**Embedded - System On Chip (SoC)** refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

### **What are Embedded - System On Chip (SoC)?**

**System On Chip (SoC)** integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

#### **Details**

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DDR, PCIe, SERDES
Connectivity	CANbus, Ethernet, I <sup>2</sup> C, SPI, UART/USART, USB
Speed	166MHz
Primary Attributes	FPGA - 90K Logic Modules
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m2s090t-fg676">https://www.e-xfl.com/product-detail/microchip-technology/m2s090t-fg676</a>

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The following table lists the embedded operating flash limits.

**Table 6 • Embedded Operating Flash Limits**

Product Grade	Element	Programming Temperature	Maximum Operating Temperature	Programming Cycles	Retention (Biased/Unbiased)
Commercial	Embedded flash	Min T <sub>J</sub> = 0 °C Max T <sub>J</sub> = 85 °C	Min T <sub>J</sub> = 0 °C Max T <sub>J</sub> = 85 °C	< 1000 cycles per page, up to two million cycles per eNVM array	20 years
				< 10000 cycles per page, up to 20 million cycles per eNVM array	10 years
Industrial	Embedded flash	Min T <sub>J</sub> = -40 °C Max T <sub>J</sub> = 100 °C	Min T <sub>J</sub> = -40 °C Max T <sub>J</sub> = 100 °C	< 1000 cycles per page, up to two million cycles per eNVM array	20 years
				< 10000 cycles per page, up to 20 million cycles per eNVM array	10 years

**Note:** If your product qualification requires accelerated programming cycles, see *Microsemi SoC Products Quality and Reliability Report* about recommended methodologies.

**Table 7 • Device Storage Temperature and Retention**

Product Grade	Storage Temperature (T <sub>stg</sub> )	Retention
Commercial	Min T <sub>J</sub> = 0 °C Max T <sub>J</sub> = 85 °C	20 years
Industrial	Min T <sub>J</sub> = -40 °C Max T <sub>J</sub> = 100 °C	20 years

**Table 8 • High Temperature Data Retention (HTR) Lifetime**

T <sub>J</sub> (C)	HTR Lifetime <sup>1</sup> (yrs)
90	20.5
95	20.5
100	20.5
105	17.0
110	15.0
115	13.0
120	11.5
125	10.0
130	8.0
135	6.0
140	4.5
145	3.0
150	1.5

1. HTR Lifetime is the period during which a verify failure is not expected due to flash leakage.

**Figure 1 • High Temperature Data Retention (HTR)****2.3.1.1 Overshoot/Undershoot Limits**

For AC signals, the input signal may undershoot during transitions to  $-1.0$  V for no longer than 10% of the period. The current during the transition must not exceed 100 mA.

For AC signals, the input signal may overshoot during transitions to  $V_{CCI} + 1.0$  V for no longer than 10% of the period. The current during the transition must not exceed 100 mA.

**Note:** The above specifications do not apply to the PCI standard. The IGLOO2 and SmartFusion2 PCI I/Os are compliant with the PCI standard including the PCI overshoot/undershoot specifications.

**2.3.1.2 Thermal Characteristics**

The temperature variable in the Microsemi SoC Products Group Designer software refers to the junction temperature, not the ambient, case, or board temperatures. This is an important distinction because dynamic and static power consumption causes the chip's junction temperature to be higher than the ambient, case, or board temperatures.

EQ1 through EQ3 give the relationship between thermal resistance, temperature gradient, and power.

$$\theta_{JA} = \frac{T_J - T_A}{P}$$

EQ 1

$$\theta_{JB} = \frac{T_J - T_B}{P}$$

EQ 2

$$\theta_{JC} = \frac{T_J - T_C}{P}$$

EQ 3

## 2.3.2 Power Consumption

The following sections describe the power consumptions of the devices.

### 2.3.2.1 Quiescent Supply Current

**Table 10 • Quiescent Supply Current Characteristics**

Power Supplies/Blocks	Modes and Configurations	
	Non-Flash*Freeze	Flash*Freeze
FPGA Core	On	Off
V <sub>DD</sub> /SERDES_[01]_VDD <sup>1</sup>	On	On
V <sub>PP</sub> /V <sub>PPNVM</sub>	On	On
HPMS_MDDR_PLL_VDDA/FDDR_PLL_VDDA/ CCC_XX[01]_PLL_VDDA/PLL0_PLL1_HPMS_MDDR_VDD A	0 V	0 V
SERDES_[01]_PLL_VDDA <sup>2</sup>	0 V	0 V
SERDES_[01]_L[0123]_VDDAPLL/VDD_2V5 <sup>2</sup>	On	On
SERDES_[01]_L[0123]_VDDAIIO <sup>2</sup>	On	On
V <sub>DDIx</sub> <sup>3, 4</sup>	On	On
V <sub>REFx</sub>	On	On
MSSDDR CLK	32 kHz	32 kHz
RAM	On	Sleep state
System controller	50 MHz	50 MHz
50 MHz oscillator (enable/disable)	Enable	Disabled
1 MHz oscillator (enable/disable)	Disabled	Disabled
Crystal oscillator (enable/disable)	Disabled	Disabled

1. SERDES\_[01]\_VDD Power Supply is shorted to V<sub>DD</sub>.
2. SerDes and DDR blocks to be unused.
3. V<sub>DDIx</sub> has been set to ON for test conditions as described. Banks on the east side should always be powered with the appropriate V<sub>DDI</sub> bank supplies. For details on bank power supplies, see "Recommendation for Unused Bank Supplies" table in the AC393: *SmartFusion2 and IGLOO2 Board Design Guidelines Application Note*.
4. No Differential (that is to say, LVDS) I/Os or ODT attributes to be used.

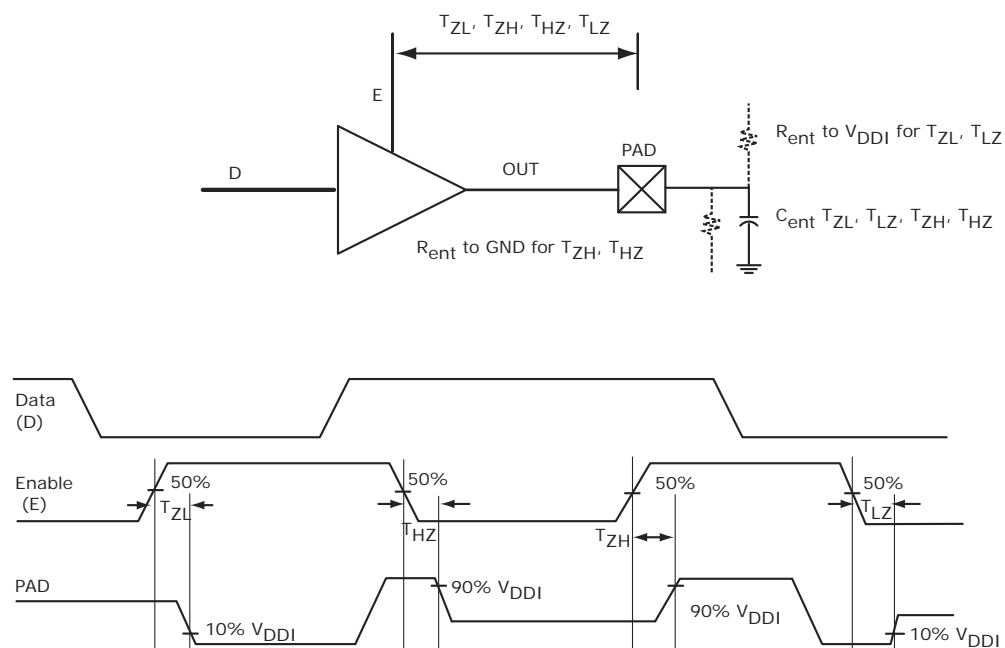
**Table 11 • SmartFusion2 and IGLOO2 Quiescent Supply Current (V<sub>DD</sub> = 1.2 V) – Typical Process**

Symbol	Modes	005	010	025	050	060	090	150	Unit	Conditions
IDC1	Non-Flash*Freeze	6.2	6.9	8.9	13.1	15.3	15.4	27.5	mA	Typical (T <sub>J</sub> = 25 °C)
		24.0	28.4	40.6	67.8	80.6	81.4	144.7	mA	Commercial (T <sub>J</sub> = 85 °C)
		35.2	41.9	60.5	102.1	121.4	122.6	219.1	mA	Industrial (T <sub>J</sub> = 100 °C)

### 2.3.5.3 Tristate Buffer and AC Loading

The tristate path for enable path loadings is described in the respective specifications. The following figure shows the methodology of characterization illustrated by the enable path test point.

**Figure 5 • Tristate Buffer for Enable Path Test Point**



### 2.3.5.4 I/O Speeds

This section describes the maximum data rate summary of I/O in worst-case industrial conditions. See the individual I/O standards for operating conditions.

**Table 18 • Maximum Data Rate Summary Table for Single-Ended I/O in Worst-Case Industrial Conditions**

I/O	MSIO	MSIOD	DDRIO	Unit
PCI 3.3 V	630			Mbps
LVTTL 3.3 V	600			Mbps
LVC MOS 3.3 V	600			Mbps
LVC MOS 2.5 V	410	420	400	Mbps
LVC MOS 1.8 V	295	400	400	Mbps
LVC MOS 1.5 V	160	220	235	Mbps
LVC MOS 1.2 V	120	160	200	Mbps
LPDDR-LVC MOS 1.8 V mode			400	Mbps

**Table 112 • SSTL2 Receiver Characteristics for MSIO I/O Bank (Input Buffers)**

	On-Die Termination (ODT)	T <sub>PY</sub>		Unit
		-1	-Std	
Pseudo differential	None	2.798	3.293	ns
True differential	None	2.733	3.215	ns

**Table 113 • DDR1/SSTL2 Receiver Characteristics for MSIOD I/O Bank (Input Buffers)**

	On-Die Termination (ODT)	T <sub>PY</sub>		Unit
		-1	-Std	
Pseudo differential	None	2.476	2.913	ns
True differential	None	2.475	2.911	ns

**Table 114 • SSTL2 Class I Transmitter Characteristics for DDRIO I/O Bank (Output and Tristate Buffers)**

	T <sub>DP</sub>		T <sub>ZL</sub>		T <sub>ZH</sub>		T <sub>HZ</sub>		T <sub>LZ</sub>		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
Single-ended	2.26	2.66	1.99	2.341	1.985	2.335	2.135	2.512	2.13	2.505	ns
Differential	2.26	2.658	2.202	2.591	2.201	2.589	2.393	2.815	2.392	2.814	ns

**Table 115 • DDR1/SSTL2 Class I Transmitter Characteristics for MSIO I/O Bank (Output and Tristate Buffers)**

	T <sub>DP</sub>		T <sub>ZL</sub>		T <sub>ZH</sub>		T <sub>HZ</sub>		T <sub>LZ</sub>		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
Single-ended	2.055	2.417	2.037	2.396	2.03	2.388	2.068	2.433	2.061	2.425	ns
Differential	2.192	2.58	2.434	2.864	2.425	2.852	2.164	2.545	2.156	2.536	ns

**Table 116 • DDR1/SSTL2 Class I Transmitter Characteristics for MSIOD I/O Bank (Output and Tristate Buffers)**

	T <sub>DP</sub>		T <sub>ZL</sub>		T <sub>ZH</sub>		T <sub>HZ</sub>		T <sub>LZ</sub>		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
Single-ended	1.512	1.779	1.462	1.72	1.462	1.72	1.676	1.972	1.676	1.971	ns
Differential	1.676	1.971	1.774	2.087	1.766	2.077	1.854	2.181	1.845	2.171	ns

**Table 117 • DDR1/SSTL2 Class II Transmitter Characteristics for DDRIO I/O Bank (Output and Tristate Buffers)**

	T <sub>DP</sub>		T <sub>ZL</sub>		T <sub>ZH</sub>		T <sub>HZ</sub>		T <sub>LZ</sub>		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
Single-ended	2.122	2.497	1.906	2.243	1.902	2.237	2.061	2.424	2.056	2.418	ns
Differential	2.127	2.501	2.042	2.402	2.043	2.403	2.363	2.78	2.365	2.781	ns

### 2.3.6.6 Low Power Double Data Rate (LPDDR)

LPDDR reduced and full drive low power double data rate standards are supported in IGLOO2 FPGA and SmartFusion2 SoC FPGA I/Os. This standard requires a differential amplifier input buffer and a push-pull output buffer.

#### Minimum and Maximum DC/AC Input and Output Levels Specification

**Table 139 • LPDDR DC Recommended DC Operating Conditions**

Parameter	Symbol	Min	Typ	Max
Supply voltage	$V_{DDI}$	1.71	1.8	1.89
Termination voltage	$V_{TT}$	0.838	0.900	0.964
Input reference voltage	$V_{REF}$	0.838	0.900	0.964

**Table 140 • LPDDR DC Input Voltage Specification**

Parameter	Symbol	Min	Max
DC input logic high	$V_{IH}$ (DC)	$0.7 \times V_{DDI}$	1.89
DC input logic low	$V_{IL}$ (DC)	-0.3	$0.3 \times V_{DDI}$
Input current high <sup>1</sup>	$I_{IH}$ (DC)		
Input current low <sup>1</sup>	$I_{IL}$ (DC)		

1. See Table 24, page 22.

**Table 141 • LPDDR DC Output Voltage Specification Reduced Drive**

Parameter	Symbol	Min	Max
DC output logic high	$V_{OH}$	$0.9 \times V_{DDI}$	
DC output logic low	$V_{OL}$		$0.1 \times V_{DDI}$
Output minimum source DC current	$I_{OH}$ at $V_{OH}$	0.1	
Output minimum sink current	$I_{OL}$ at $V_{OL}$	-0.1	

**Table 142 • LPDDR DC Output Voltage Specification Full Drive<sup>1</sup>**

Parameter	Symbol	Min	Max
DC output logic high	$V_{OH}$	$0.9 \times V_{DDI}$	
DC output logic low	$V_{OL}$		$0.1 \times V_{DDI}$
Output minimum source DC current	$I_{OH}$ at $V_{OH}$	0.1	
Output minimum sink current	$I_{OL}$ at $V_{OL}$	-0.1	

1. To meet JEDEC Electrical Compliance, use LPDDR Full Drive Transmitter.

**Table 143 • LPDDR DC Differential Voltage Specification**

Parameter	Symbol	Min
DC input differential voltage	$V_{ID}$ (DC)	$0.4 \times V_{DDI}$



**Table 144 • LPDDR AC Differential Voltage Specifications (for DDRIO I/O Bank Only)**

Parameter	Symbol	Min	Max	Unit
AC input differential voltage	$V_{DIFF}$	$0.6 \times V_{DDI}$		V
AC differential cross point voltage	$V_x$	$0.4 \times V_{DDI}$	$0.6 \times V_{DDI}$	V

**Table 145 • LPDDR AC Specifications (for DDRIO I/O Bank Only)**

Parameter	Symbol	Max	Unit	Conditions
Maximum data rate	$D_{MAX}$	400	Mbps	AC loading: per JEDEC specifications

**Table 146 • LPDDR AC Calibrated Impedance Option (for DDRIO I/O Bank Only)**

Parameter	Symbol	Typ	Unit	Conditions
Supported output driver calibrated impedance	$R_{REF}$	20, 42	$\Omega$	Reference resistor = 150 $\Omega$
Effective impedance value (ODT)	$R_{TT}$	50, 70, 150	$\Omega$	Reference resistor = 150 $\Omega$

**Table 147 • LPDDR AC Test Parameter Specifications (for DDRIO I/O Bank Only)**

Parameter	Symbol	Typ	Unit
Measuring/trip point for data path	$V_{TRIP}$	0.9	V
Resistance for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$R_{ENT}$	2K	$\Omega$
Capacitive loading for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$C_{ENT}$	5	pF
Reference resistance for data test path for LPDDR ( $T_{DP}$ )	$R_{TT\_TEST}$	50	$\Omega$
Capacitive loading for data path ( $T_{DP}$ )	$C_{LOAD}$	5	$\Omega$

**AC Switching Characteristics**

Worst-case commercial conditions:  $T_J = 85^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ , worst-case  $V_{DDI}$ .

**Table 148 • LPDDR Receiver Characteristics for DDRIO I/O Bank with Fixed Codes**

	On-Die Termination (ODT)	$T_{PY}$		Unit
		-1	-Std	
Pseudo differential	None	1.568	1.845	ns
True differential	None	1.588	1.869	ns

**Table 149 • LPDDR Reduced Drive for DDRIO I/O Bank (Output and Tristate Buffers)**

	$T_{DP}$		$T_{ENZL}$		$T_{ENZH}$		$T_{ENHZ}$		$T_{ENLZ}$		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
Single-ended	2.383	2.804	2.23	2.623	2.229	2.622	2.202	2.591	2.201	2.59	ns
Differential	2.396	2.819	2.764	3.252	2.764	3.252	2.255	2.653	2.255	2.653	ns

**Table 162 • LVDS DC Output Voltage Specification**

Parameter	Symbol	Min	Typ	Max	Unit
DC output logic high	$V_{OH}$	1.25	1.425	1.6	V
DC output logic low	$V_{OL}$	0.9	1.075	1.25	V

**Table 163 • LVDS DC Differential Voltage Specification**

Parameter	Symbol	Min	Typ	Max	Unit
Differential output voltage swing	$V_{OD}$	250	350	450	mV
Output common mode voltage	$V_{OCM}$	1.125	1.25	1.375	V
Input common mode voltage	$V_{ICM}$	0.05	1.25	2.35	V
Input differential voltage	$V_{ID}$	100	350	600	mV

**Table 164 • LVDS Minimum and Maximum AC Switching Speed**

Parameter	Symbol	Max	Unit	Conditions
Maximum data rate (for MSIO I/O bank)	$D_{MAX}$	535	Mbps	AC loading: 12 pF / 100 $\Omega$ differential load
Maximum data rate (for MSIOD I/O bank) no pre-emphasis	$D_{MAX}$	620	Mbps	AC loading: 10 pF / 100 $\Omega$ differential load
		700	Mbps	AC loading: 2 pF / 100 $\Omega$ differential load

**Table 165 • LVDS AC Impedance Specifications**

Parameter	Symbol	Typ	Max	Unit
Termination resistance	$R_T$	100		$\Omega$

**Table 166 • LVDS AC Test Parameter Specifications**

Parameter	Symbol	Typ	Unit
Measuring/trip point for data path	$V_{TRIP}$	Cross point	V
Resistance for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$R_{ENT}$	2K	$\Omega$
Capacitive loading for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$C_{ENT}$	5	pF

**LVDS25 AC Switching Characteristics**

 Worst commercial-case conditions:  $T_J = 85^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ ,  $V_{DDI} = 2.375\text{ V}$ 
**Table 167 • LVDS25 Receiver Characteristics for MSIO I/O Bank (Input Buffers)**

On-Die Termination (ODT)	$T_{PY}$		Unit
	-1	-Std	
None	2.774	3.263	ns
100	2.775	3.264	ns

**Table 185 • M-LVDS DC Voltage Specification Output Voltage Specification (for MSIO I/O Bank Only)**

Parameter	Symbol	Min	Typ	Max	Unit
DC output logic high	$V_{OH}$	1.25	1.425	1.6	V
DC output logic low	$V_{OL}$	0.9	1.075	1.25	V

**Table 186 • M-LVDS Differential Voltage Specification**

Parameter	Symbol	Min	Max	Unit
Differential output voltage swing (for MSIO I/O bank only)	$V_{OD}$	300	650	mV
Output common mode voltage (for MSIO I/O bank only)	$V_{OCM}$	0.3	2.1	V
Input common mode voltage	$V_{ICM}$	0.3	1.2	V
Input differential voltage	$V_{ID}$	50	2400	mV

**Table 187 • M-LVDS Minimum and Maximum AC Switching Speed for MSIO I/O Bank**

Parameter	Symbol	Max	Unit	Conditions
Maximum data rate	$D_{MAX}$	500	Mbps	AC loading: 2 pF / 100 $\Omega$ differential load

**Table 188 • M-LVDS AC Impedance Specifications**

Parameter	Symbol	Typ	Unit
Termination resistance	$R_T$	50	$\Omega$

**Table 189 • M-LVDS AC Test Parameter Specifications**

Parameter	Symbol	Typ	Unit
Measuring/trip point for data path	$V_{TRIP}$	Cross point	V
Resistance for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$R_{ENT}$	2K	$\Omega$
Capacitive loading for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$C_{ENT}$	5	pF

**AC Switching Characteristics**

Worst commercial-case conditions:  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ ,  $V_{DDI} = 2.375\text{ V}$

**Table 190 • M-LVDS AC Switching Characteristics for Receiver (for MSIO I/O Bank - Input Buffers)**

On-Die Termination (ODT)	$T_{PY}$		Unit
	-1	-Std	
None	2.738	3.221	ns
100	2.735	3.218	ns

### 2.3.10.2 Timing Characteristics

The following table lists the combinatorial cell propagation delays in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

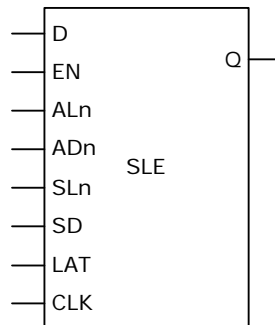
**Table 223 • Combinatorial Cell Propagation Delays**

Combinatorial Cell	Equation	Symbol	-1	-Std	Unit
INV	$Y = !A$	$T_{PD}$	0.1	0.118	ns
AND2	$Y = A \cdot B$	$T_{PD}$	0.164	0.193	ns
NAND2	$Y = !(A \cdot B)$	$T_{PD}$	0.147	0.173	ns
OR2	$Y = A + B$	$T_{PD}$	0.164	0.193	ns
NOR2	$Y = !(A + B)$	$T_{PD}$	0.147	0.173	ns
XOR2	$Y = A \oplus B$	$T_{PD}$	0.164	0.193	ns
XOR3	$Y = A \oplus B \oplus C$	$T_{PD}$	0.225	0.265	ns
AND3	$Y = A \cdot B \cdot C$	$T_{PD}$	0.209	0.246	ns
AND4	$Y = A \cdot B \cdot C \cdot D$	$T_{PD}$	0.287	0.338	ns

### 2.3.10.3 Sequential Module

IGLOO2 and SmartFusion2 SoC FPGAs offer a separate flip-flop which can be used independently from the LUT. The flip-flop can be configured as a register or a latch and has a data input and optional enable, synchronous load (clear or preset), and asynchronous load (clear or preset).

**Figure 15 • Sequential Module**



### 2.3.12.2 FPGA Fabric Micro SRAM ( $\mu$ SRAM)

The following table lists the  $\mu$ SRAM in  $64 \times 18$  mode in worst commercial-case conditions when  $T_J = 85^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 237 •  $\mu$ SRAM (RAM64x18) in  $64 \times 18$  Mode**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read clock period	$T_{CY}$	4		4		ns
Read clock minimum pulse width high	$T_{CLKMPWH}$	1.8		1.8		ns
Read clock minimum pulse width low	$T_{CLKMPWL}$	1.8		1.8		ns
Read pipeline clock period	$T_{PLCY}$	4		4		ns
Read pipeline clock minimum pulse width high	$T_{PLCLKMPWH}$	1.8		1.8		ns
Read pipeline clock minimum pulse width low	$T_{PLCLKMPWL}$	1.8		1.8		ns
Read access time with pipeline register	$T_{CLK2Q}$		0.266		0.313	ns
Read access time without pipeline register				1.677		1.973
Read address setup time in synchronous mode	$T_{ADDRSU}$	0.301		0.354		ns
Read address setup time in asynchronous mode			1.856		2.184	
Read address hold time in synchronous mode	$T_{ADDRHD}$	0.091		0.107		ns
Read address hold time in asynchronous mode			-0.778		-0.915	
Read enable setup time	$T_{RDENSU}$	0.278		0.327		ns
Read enable hold time	$T_{RDENHD}$	0.057		0.067		ns
Read block select setup time	$T_{BLKSU}$	1.839		2.163		ns
Read block select hold time	$T_{BLKHD}$	-0.65		-0.765		ns
Read block select to out disable time (when pipelined register is disabled)	$T_{BLK2Q}$		2.036		2.396	ns
Read asynchronous reset removal time (pipelined clock)	$T_{RSTREM}$	-0.023		-0.027		ns
Read asynchronous reset removal time (non-pipelined clock)			0.046		0.054	
Read asynchronous reset recovery time (pipelined clock)	$T_{RSTREC}$	0.507		0.597		ns
Read asynchronous reset recovery time (non-pipelined clock)			0.236		0.278	
Read asynchronous reset to output propagation delay (with pipelined register enabled)	$T_{R2Q}$		0.839		0.987	ns
Read synchronous reset setup time	$T_{SRSTSU}$	0.271		0.319		ns
Read synchronous reset hold time	$T_{SRSTHD}$	0.061		0.071		ns
Write clock period	$T_{CCY}$	4		4		ns
Write clock minimum pulse width high	$T_{CCLKMPWH}$	1.8		1.8		ns
Write clock minimum pulse width low	$T_{CCLKMPWL}$	1.8		1.8		ns
Write block setup time	$T_{BLKCSU}$	0.404		0.476		ns
Write block hold time	$T_{BLKCHD}$	0.007		0.008		ns
Write input data setup time	$T_{DINCSU}$	0.115		0.135		ns
Write input data hold time	$T_{DINCHD}$	0.15		0.177		ns

**Table 237 •  $\mu$ SRAM (RAM64x18) in 64 × 18 Mode (continued)**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Write address setup time	$T_{ADDRCSU}$	0.088		0.104		ns
Write address hold time	$T_{ADDRCHD}$	0.128		0.15		ns
Write enable setup time	$T_{WECSU}$	0.397		0.467		ns
Write enable hold time	$T_{WECHD}$	-0.026		-0.03		ns
Maximum frequency	$F_{MAX}$		250		250	MHz

The following table lists the  $\mu$ SRAM in 64 × 16 mode in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 238 •  $\mu$ SRAM (RAM64x16) in 64 × 16 Mode**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read clock period	$T_{CY}$	4		4		ns
Read clock minimum pulse width high	$T_{CLKMPWH}$	1.8		1.8		ns
Read clock minimum pulse width low	$T_{CLKMPWL}$	1.8		1.8		ns
Read pipeline clock period	$T_{PLCY}$	4		4		ns
Read pipeline clock minimum pulse width high	$T_{PLCLKMPWH}$	1.8		1.8		ns
Read pipeline clock minimum pulse width low	$T_{PLCLKMPWL}$	1.8		1.8		ns
Read access time with pipeline register	$T_{CLK2Q}$		0.266		0.313	ns
Read access time without pipeline register				1.677		1.973
Read address setup time in synchronous mode	$T_{ADDRSU}$	0.301		0.354		ns
Read address setup time in asynchronous mode			1.856		2.184	
Read address hold time in synchronous mode	$T_{ADDRHD}$	0.091		0.107		ns
Read address hold time in asynchronous mode			-0.778		-0.915	
Read enable setup time	$T_{RDENSU}$	0.278		0.327		ns
Read enable hold time	$T_{RDENHD}$	0.057		0.067		ns
Read block select setup time	$T_{BLKSU}$	1.839		2.163		ns
Read block select hold time	$T_{BLKHD}$	-0.65		-0.765		ns
Read block select to out disable time (when pipelined register is disabled)	$T_{BLK2Q}$		2.036		2.396	ns
Read asynchronous reset removal time (pipelined clock)	$T_{RSTREM}$	-0.023		-0.027		ns
Read asynchronous reset removal time (non-pipelined clock)			0.046		0.054	
Read asynchronous reset recovery time (pipelined clock)	$T_{RSTREC}$	0.507		0.597		ns
Read asynchronous reset recovery time (non-pipelined clock)			0.236		0.278	
Read asynchronous reset to output propagation delay (with pipelined register enabled)	$T_{R2Q}$		0.835		0.983	ns
Read synchronous reset setup time	$T_{SRSTSU}$	0.271		0.319		ns

**Table 243 •  $\mu$ SRAM (RAM1024x1) in 1024 x 1 Mode (continued)**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read asynchronous reset recovery time (pipelined clock)	$T_{RSTREC}$	0.507		0.597		ns
Read asynchronous reset recovery time (non-pipelined clock)		0.236		0.278		ns
Read asynchronous reset to output propagation delay (with pipelined register enabled)	$T_{R2Q}$		0.83		0.98	ns
Read synchronous reset setup time	$T_{SRSTSU}$	0.271		0.319		ns
Read synchronous reset hold time	$T_{SRSTHD}$	0.061		0.071		ns
Write clock period	$T_{CCY}$	4		4		ns
Write clock minimum pulse width high	$T_{CCLKMPWH}$	1.8		1.8		ns
Write clock minimum pulse width low	$T_{CCLKMPWL}$	1.8		1.8		ns
Write block setup time	$T_{BLKCSU}$	0.404		0.476		ns
Write block hold time	$T_{BLKCHD}$	0.007		0.008		ns
Write input data setup time	$T_{DINCSU}$	0.003		0.004		ns
Write input data hold time	$T_{DINCHD}$	0.137		0.161		ns
Write address setup time	$T_{ADDRCSU}$	0.088		0.104		ns
Write address hold time	$T_{ADDRCHD}$	0.247		0.29		ns
Write enable setup time	$T_{WECSU}$	0.397		0.467		ns
Write enable hold time	$T_{WECHD}$	-0.03		-0.03		ns
Maximum frequency	$F_{MAX}$		250		250	MHz

### 2.3.13 Programming Times

The following tables list the programming times in typical conditions when  $T_J = 25\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.2\text{ V}$ . External SPI flash part# AT25DF641-s3H is used during this measurement.

**Table 244 • JTAG Programming (Fabric Only)**

M2S/M2GL				
Device	Image size Bytes	Program	Verify	Unit
005	302672	22	10	Sec
010	568784	28	18	Sec
025	1223504	51	26	Sec
050	2424832	66	54	Sec
060	2418896	77	54	Sec
090	3645968	113	126	Sec
150	6139184	155	193	Sec

**Table 251 • SmartFusion2 Cortex-M3 ISP Programming (eNVM Only) (continued)**

M2S/M2GL Device	Image size Bytes	Authenticate	Program	Verify	Unit
150	544496	10	158	15	Sec

**Table 252 • SmartFusion2 Cortex-M3 ISP Programming (Fabric and eNVM)**

M2S/M2GL Device	Image size Bytes	Authenticate	Program	Verify	Unit
005	439296	9	61	11	Sec
010	842688	15	107	21	Sec
025	1497408	26	121	35	Sec
050	2695168	43	141	55	Sec
060	2686464	48	143	60	Sec
090	4190208	75	244	91	Sec
150	6682768	117	296	141	Sec

**Table 253 • Programming Times with 100 kHz, 25 MHz, and 12.5 MHz SPI Clock Rates (Fabric Only)**

M2S/M2GL Device	Auto Programming	Auto Update	Programming Recovery	Unit
	100 kHz	25 MHz	12.5 MHz	
005	47	27	28	Sec
010	77	35	35	Sec
025	150	42	41	Sec
050	33 <sup>1</sup>	Not Supported	Not Supported	Sec
060	291	83	82	Sec
090	427	109	108	Sec
150	708	157	160	Sec

1. Auto Programming in 050 device is done through SC\_SPI, and SPI CLK is set to 6.25 MHz.

**Table 254 • Programming Times with 100 kHz, 25 MHz, and 12.5 MHz SPI Clock Rates (eNVM Only)**

M2S/M2GL Device	Auto Programming	Auto Update	Programming Recovery	Unit
	100 kHz	25 MHz	12.5 MHz	
005	41	48	49	Sec
010	86	87	87	Sec
025	87	85	86	Sec
050	85	Not Supported	Not Supported	Sec
060	78	86	86	Sec
090	154	162	162	Sec



**Table 259 • 2 Step IAP Programming (Fabric Only)**

M2S/M2GL Device	Image size		Authenticate	Program	Verify	Unit
	Bytes					
005	302672	4	39	6	Sec	
010	568784	7	45	12	Sec	
025	1223504	14	55	23	Sec	
050	2424832	29	74	40	Sec	
060	2418896	39	83	50	Sec	
090	3645968	60	106	73	Sec	
150	6139184	100	154	120	Sec	

**Table 260 • 2 Step IAP Programming (eNVM Only)**

M2S/M2GL Device	Image size		Authenticate	Program	Verify	Unit
	Bytes					
005	137536	2	59	5	Sec	
010	274816	4	98	11	Sec	
025	274816	4	100	10	Sec	
050	2,78,528	3	107	9	Sec	
060	268480	5	98	22	Sec	
090	544496	10	174	43	Sec	
150	544496	10	175	44	Sec	

**Table 261 • 2 Step IAP Programming (Fabric and eNVM)**

M2S/M2GL Device	Image size		Authenticate	Program	Verify	Unit
	Bytes					
005	439296	6	78	11	Sec	
010	842688	11	122	21	Sec	
025	1497408	19	135	32	Sec	
050	2695168	32	158	48	Sec	
060	2686464	43	159	70	Sec	
090	4190208	68	258	115	Sec	
150	6682768	109	308	162	Sec	

The following table lists the system controller characteristics in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 286 • System Controller SPI Characteristics for All Devices**

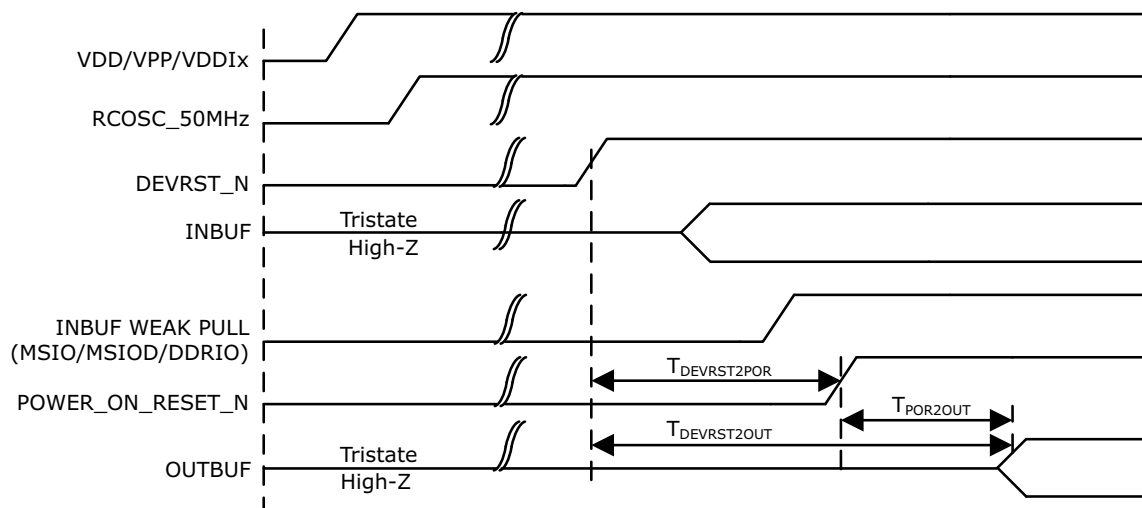
Symbol	Description	Conditions	Min	Typ	Unit
sp1	SC_SPI_SCK minimum period		20		ns
sp2	SC_SPI_SCK minimum pulse width high		10		ns
sp3	SC_SPI_SCK minimum pulse width low		10		ns
sp4 <sup>1</sup>	SC_SPI_SCK, SC_SPI_SDO, SC_SPI_SS rise time (10%–90%) 1	I/O configuration: LVTTTL 3.3 V–20 mA AC loading: 35 pF Test conditions: Typical voltage, 25 °C		1.239	ns
sp5 <sup>1</sup>	SC_SPI_SCK, SC_SPI_SDO, SC_SPI_SS fall time (10%–90%) 1	I/O configuration: LVTTTL 3.3 V–20 mA AC loading: 35 pF Test conditions: Typical voltage, 25 °C		1.245	ns
sp6	Data from master (SC_SPI_SDO) setup time		160		ns
sp7	Data from master (SC_SPI_SDO) hold time		160		ns
sp8	SC_SPI_SDI setup time		20		ns
sp9	SC_SPI_SDI hold time		20		ns

- For specific Rise/Fall Times, board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: <http://www.microsemi.com/soc/download/ibis/default.aspx>. Use the supported I/O Configurations for the System Controller SPI in the following table.

**Table 287 • Supported I/O Configurations for System Controller SPI (for MSIO Bank Only)**

Voltage Supply	I/O Drive Configuration	Unit
3.3 V	20	mA
2.5 V	16	mA
1.8 V	12	mA
1.5 V	8	mA
1.2 V	4	mA

Figure 20 • DEVRST\_N to Functional Timing Diagram for IGLOO2



### 2.3.27 Flash\*Freeze Timing Characteristics

The following table lists the Flash\*Freeze entry and exit times in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

Table 293 • Flash\*Freeze Entry and Exit Times

Parameter	Symbol	Entry/Exit Timing			Unit	Conditions
		FCLK = 100MHz		FCLK = 3 MHz		
		005, 010, 025, 060, 090, and 150	050	All Devices		
Entry time	TFF_ENTRY	160	150	320	$\mu\text{s}$	eNVM and MSS/HPMS PLL = ON
		215	200	430	$\mu\text{s}$	eNVM and MSS/HPMS PLL= OFF
Exit time with respect to the MSS PLL Lock	TFF_EXIT	100	100	140	$\mu\text{s}$	eNVM and MSS/HPMS PLL = ON during F*F
		136	120	190	$\mu\text{s}$	eNVM = ON and MSS/HPMS PLL = OFF during F*F and MSS/HPMS PLL turned back on at exit
		200	200	285	$\mu\text{s}$	eNVM and MSS/HPMS PLL = OFF during F*F and both are turned back on at exit
		200	200	285	$\mu\text{s}$	eNVM = OFF and MSS/HPMS PLL = ON during F*F and eNVM turned back on at exit

The following table lists the receiver pa in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 297 • Receiver Parameters**

Symbol	Description	Min	Typ	Max	Unit
VRX-IN-PP-CC	Differential input peak-to-peak sensitivity (2.5 Gbps)	0.238		1.2	V
	Differential input peak-to-peak sensitivity (2.5 Gbps, de-emphasized)	0.219		1.2	V
	Differential input peak-to-peak sensitivity (5.0 Gbps)	0.300		1.2	V
	Differential input peak-to-peak sensitivity (5.0 Gbps, de-emphasized)	0.300		1.2	V
VRX-CM-AC-P	Input common mode range (AC coupled)			150	mV
ZRX-DIFF-DC	Differential input termination	80	100	120	$\Omega$
REXT	External calibration resistor	1,188	1,200	1,212	$\Omega$
CDR-LOCK-RST	CDR relock time from reset			15	$\mu\text{s}$
RLRX-DIFF	Return loss differential mode (2.5 Gbps)	-10			dB
	Return loss differential mode (5.0 Gbps)				
	0.05 GHz to 1.25 GHz	-10			dB
	1.25 GHz to 2.5 GHz	-8			dB
RLRX-CM	Return loss common mode (2.5 Gbps, 5.0 Gbps)	-6			dB
RX-CID <sup>1</sup>	CID limit PCIe Gen1/2			200	UI
VRX-IDLE-DET-DIFF-PP	Signal detect limit	65		175	mV

1. AC-coupled, BER =  $e^{-12}$ , using synchronous clock.

**Table 298 • SerDes Protocol Compliance**

Protocol	Maximum Data Rate (Gbps)	-1	-Std
PCIe Gen 1	2.5	Yes	Yes
PCIe Gen 2	5.0	Yes	
XAUI	3.125	Yes	
Generic EPCS	3.2	Yes	
Generic EPCS	2.5	Yes	Yes

The following table lists the SerDes reference clock AC specifications in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 299 • SerDes Reference Clock AC Specifications**

Parameter	Symbol	Min	Max	Unit
Reference clock frequency	$F_{REFCLK}$	100	160	MHz
Reference clock rise time	$T_{RISE}$	0.6	4	V/ns
Reference clock fall time	$T_{FALL}$	0.6	4	V/ns
Reference clock duty cycle	$T_{CYC}$	40	60	%
Reference clock mismatch	$M_{MREFCLK}$	-300	300	ppm
Reference spread spectrum clock	$SSC_{ref}$	0	5000	ppm

**Table 300 • HCSL Minimum and Maximum DC Input Levels (Applicable to SerDes REFCLK Only)**

Parameter	Symbol	Min	Typ	Max	Unit
<b>Recommended DC Operating Conditions</b>					
Supply voltage	$V_{DDI}$	2.375	2.5	2.625	V
<b>HCSL DC Input Voltage Specification</b>					
DC Input voltage	$V_I$	0		2.625	V
<b>HCSL Differential Voltage Specification</b>					
Input common mode voltage	$V_{ICM}$	0.05		2.4	V
Input differential voltage	$V_{IDIFF}$	100		1100	mV

**Table 301 • HCSL Minimum and Maximum AC Switching Speeds (Applicable to SerDes REFCLK Only)**

Parameter	Symbol	Min	Typ	Max	Unit
<b>HCSL AC Specifications</b>					
Maximum data rate (for MSIO I/O bank)	$F_{MAX}$			350	Mbps
<b>HCSL Impedance Specifications</b>					
Termination resistance	$R_t$		100		$\Omega$

## 2.3.31 SmartFusion2 Specifications

### 2.3.31.1 MSS Clock Frequency

The following table lists the maximum frequency for MSS main clock in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 302 • Maximum Frequency for MSS Main Clock**

Symbol	Description	-1	-Std	Unit
M3_CLK	Maximum frequency for the MSS main clock	166	142	MHz